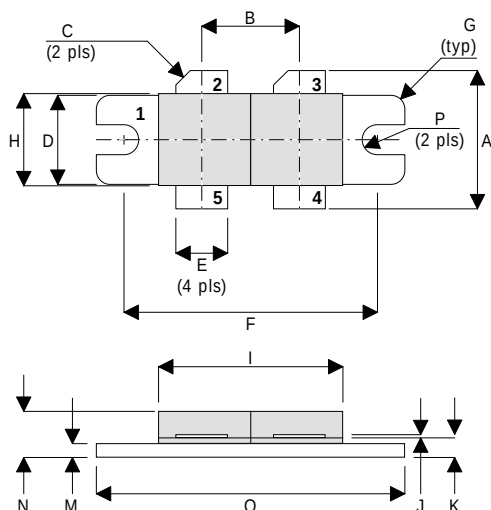


MECHANICAL DATA

TetraFET 100W – 28V – 900MHz



DIM	mm	Tol.	Inches	Tol.
A	19.05	0.50	0.75	0.020
B	10.77	0.13	0.424	0.005
C	45°	5°	45°	5°
D	9.78	0.13	0.385	0.005
E	5.71	0.13	0.225	0.005
F	27.94	0.13	1.100	0.005
G	1.52R	0.13	0.060R	0.005
H	10.16	0.13	0.400	0.005
I	22.22	MAX	0.875	MAX
J	0.13	0.02	0.005	0.001
K	2.72	0.13	0.107	0.005
M	1.70	0.13	0.067	0.005
N	5.08	0.50	0.200	0.020
O	34.03	0.13	1.340	0.005
P	1.61R	0.08	0.064R	0.003

PIN 1 SOURCE (COMMON) PIN 2 DRAIN 1
PIN 3 DRAIN 2 PIN 4 GATE 2
PIN 5 GATE 1

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
PER SIDE					
BV_{DSS} Drain-Source Breakdown Voltage	$I = 100\text{mA}$	65			V
I_{DSS} Zero Gate Voltage Drain Current	$V = 28\text{V}$			4	mA
I_{GSS} Gate Leakage Current	$V = 20\text{V}$			1	μA
$V_{GS(th)}$ Gate Threshold Voltage	$I = 10\text{mA}$	1		7	V
g_m *	$V = 10\text{V}$ $I = 3\text{A}$ $T = 300\mu\text{S}$		3.2		mhos
C_{iss} Input Capacitance	$V_{DS} = 0\text{V}$ $V_{GS} = -5\text{V}$		170		pF
C_{oss} Output Capacitance	$V = 28\text{V}$		68		pF
C_{rss} Reverse Transfer Capacitance	$V = 28\text{V}$		3.6		pF
$V_{GS(th)match}$ Gate Threshold Matching Voltage Between Sides	$I_D = 10\text{mA}$ $V_{DS} = V_{GS}$			0.1	V
TOTAL DEVICE					
$P_O = 100\text{W}$ $f = 900\text{MHz}$ $V = 28\text{V}$ $I_{DQ} = 3\text{A}$					
Thermal Resistance = $0.6^{\circ}\text{C} / \text{W}$					

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.